

# BSS138L, BVSS138L

## Power MOSFET 200 mA, 50 V

### N-Channel SOT-23

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### Features

- Low Threshold Voltage ( $V_{GS(th)}$ : 0.85 V–1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	50	Vdc
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 20$	Vdc
Drain Current			mA
– Continuous @ $T_A = 25^\circ\text{C}$	$I_D$	200	
– Pulsed Drain Current ( $t_p \leq 10 \mu\text{s}$ )	$I_{DM}$	800	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	$T_L$	260	$^\circ\text{C}$

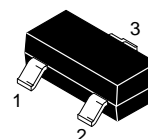
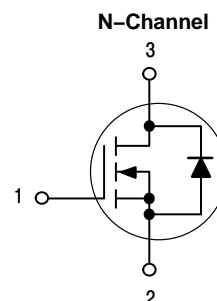
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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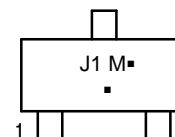
[www.onsemi.com](http://www.onsemi.com)

200 mA, 50 V  
 $R_{DS(on)} = 3.5 \Omega$



SOT-23  
CASE 318  
STYLE 21

#### MARKING DIAGRAM



J1 = Device Code  
M = Date Code\*  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
BSS138LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BVSS138LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BSS138LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
BVSS138LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μAdc)	V <sub>(BR)DSS</sub>	50	–	–	Vdc
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0 Vdc, 25°C) (V <sub>DS</sub> = 50 Vdc, V <sub>GS</sub> = 0 Vdc, 25°C) (V <sub>DS</sub> = 50 Vdc, V <sub>GS</sub> = 0 Vdc, 150°C)	I <sub>DSS</sub>	–	–	0.1 0.5 5.0	μAdc
Gate-Source Leakage Current (V <sub>GS</sub> = ± 20 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	–	–	±0.1	μAdc

### ON CHARACTERISTICS (Note 1)

Gate-Source Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0 mAdc)	V <sub>GS(th)</sub>	0.85	–	1.5	Vdc
Static Drain-to-Source On-Resistance (V <sub>GS</sub> = 2.75 Vdc, I <sub>D</sub> < 200 mAdc, T <sub>A</sub> = –40°C to +85°C) (V <sub>GS</sub> = 5.0 Vdc, I <sub>D</sub> = 200 mAdc)	r <sub>DS(on)</sub>	–	5.6	10 3.5	Ω
Forward Transconductance (V <sub>DS</sub> = 25 Vdc, I <sub>D</sub> = 200 mAdc, f = 1.0 kHz)	g <sub>fs</sub>	100	–	–	mmhos

### DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1 MHz)	C <sub>iss</sub>	–	40	50	pF
Output Capacitance	(V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1 MHz)	C <sub>oss</sub>	–	12	25	
Transfer Capacitance	(V <sub>DG</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1 MHz)	C <sub>rss</sub>	–	3.5	5.0	

### SWITCHING CHARACTERISTICS (Note 2)

Turn-On Delay Time	(V <sub>DD</sub> = 30 Vdc, I <sub>D</sub> = 0.2 Adc,)	t <sub>d(on)</sub>	–	–	20	ns
Turn-Off Delay Time		t <sub>d(off)</sub>	–	–	20	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

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## TYPICAL ELECTRICAL CHARACTERISTICS

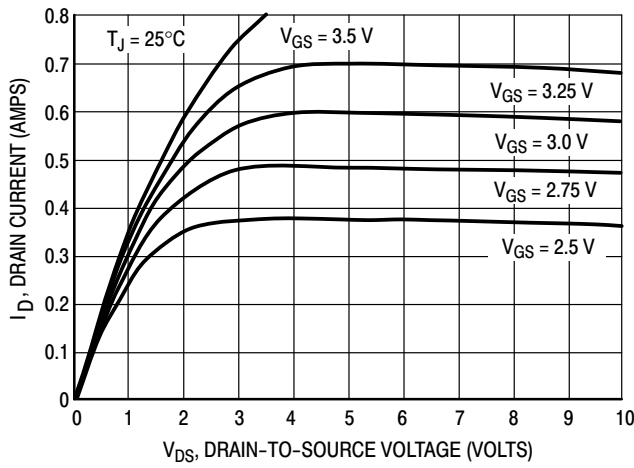


Figure 1. On-Region Characteristics

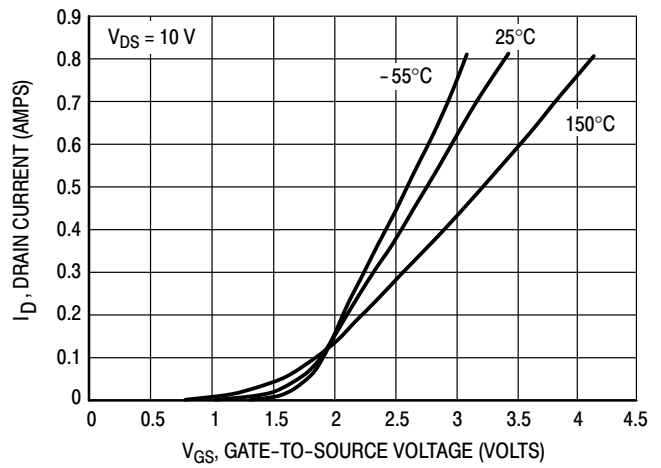


Figure 2. Transfer Characteristics

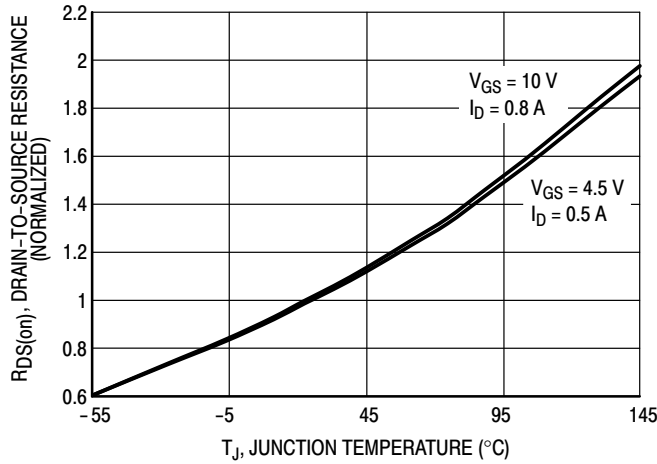


Figure 3. On-Resistance Variation with Temperature

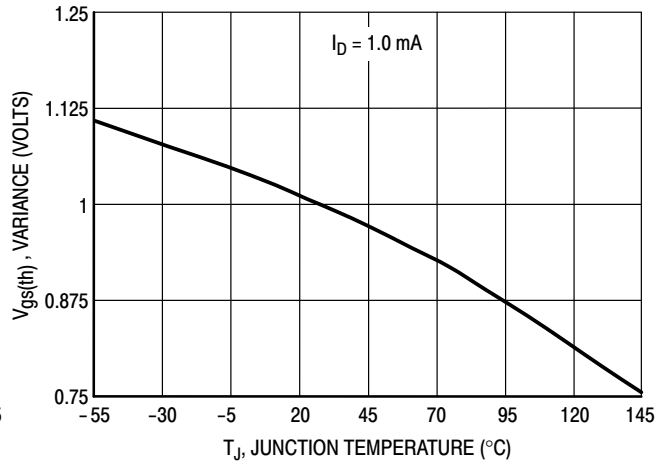


Figure 4. Threshold Voltage Variation with Temperature

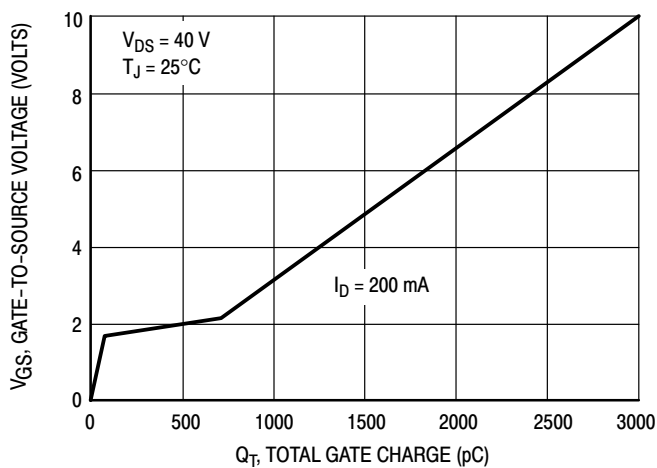


Figure 5. Gate Charge

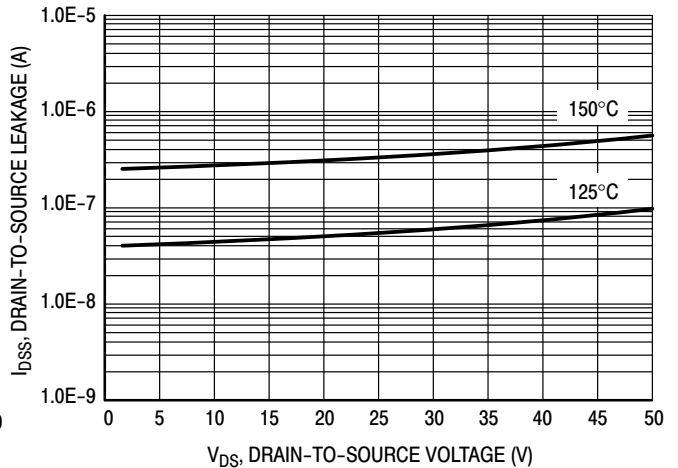


Figure 6. IDSS

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## TYPICAL ELECTRICAL CHARACTERISTICS

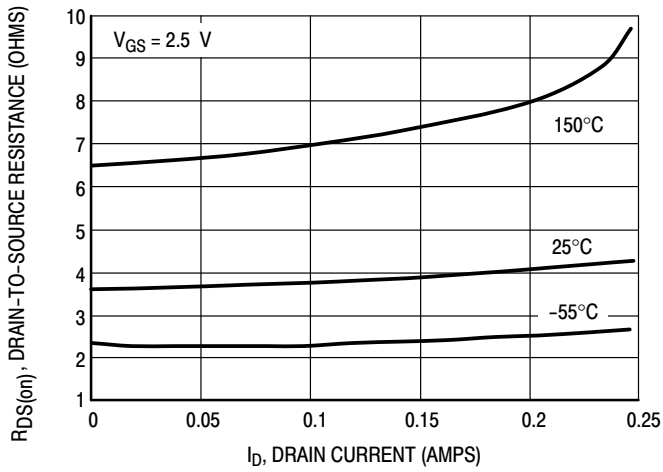


Figure 7. On-Resistance versus Drain Current

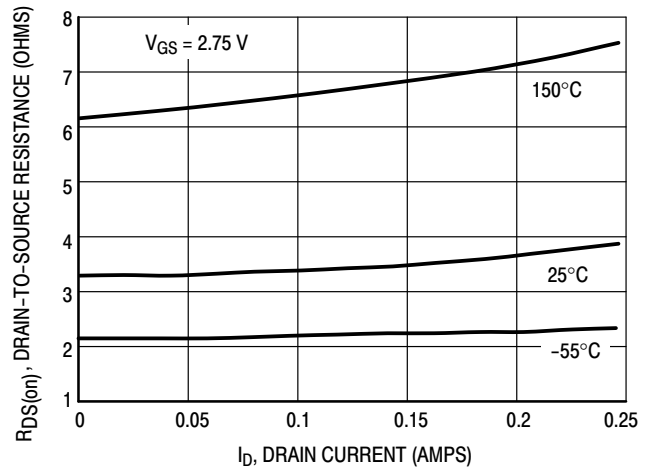


Figure 8. On-Resistance versus Drain Current

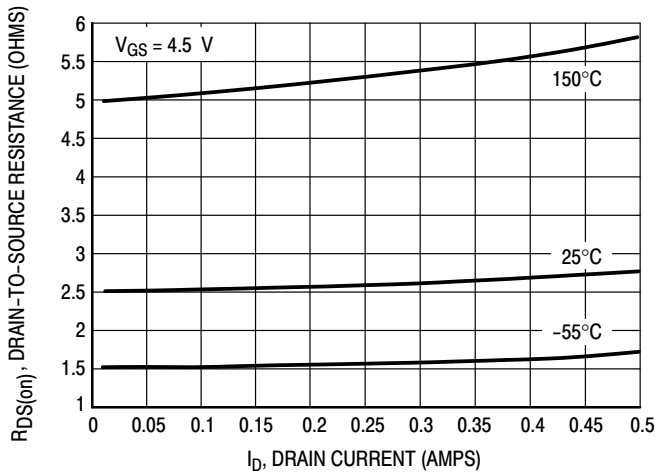


Figure 9. On-Resistance versus Drain Current

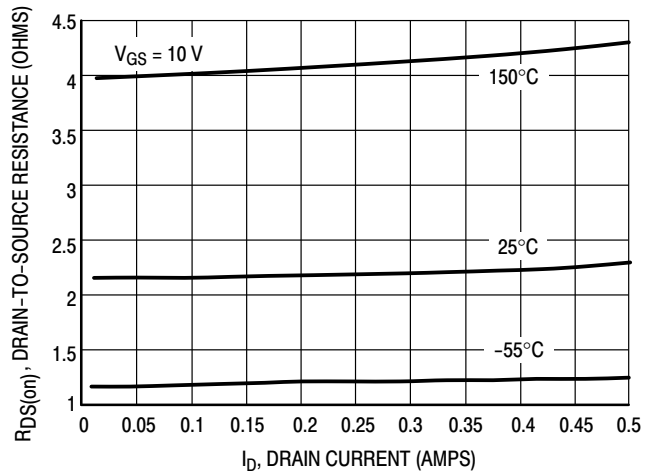


Figure 10. On-Resistance versus Drain Current

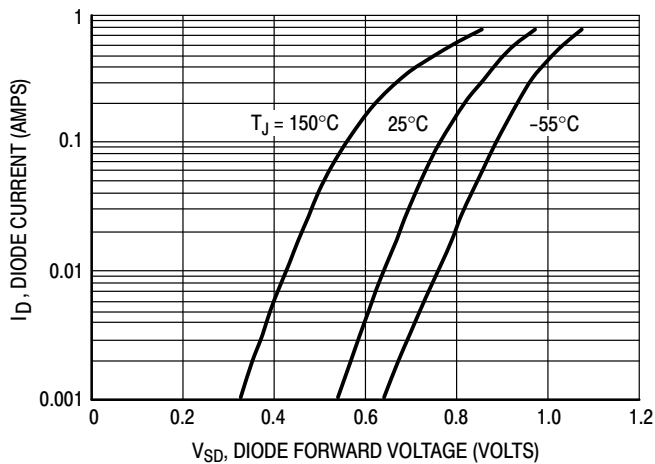


Figure 11. Body Diode Forward Voltage

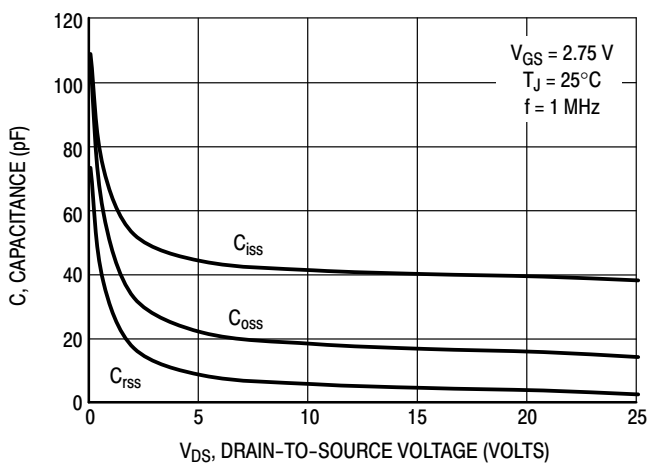
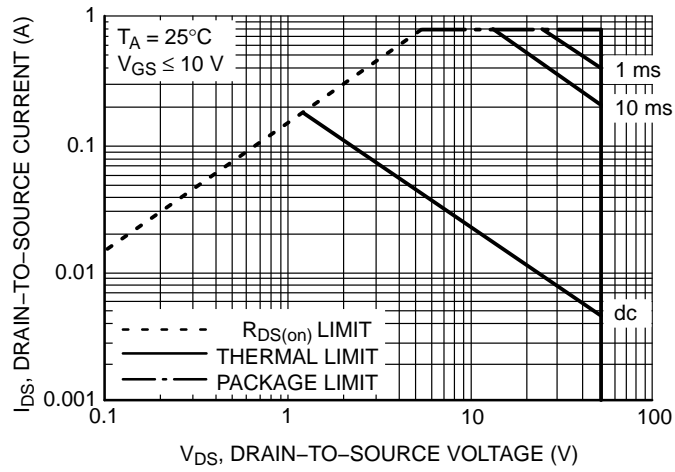


Figure 12. Capacitance

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## TYPICAL ELECTRICAL CHARACTERISTICS

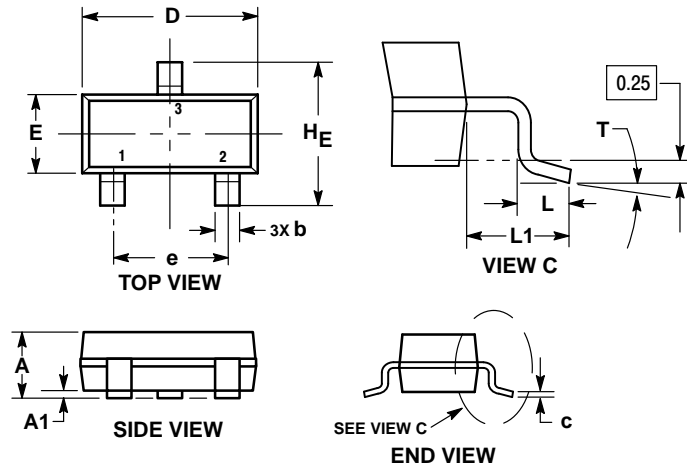


**Figure 13. Safe Operating Area**

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## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AR



NOTES:

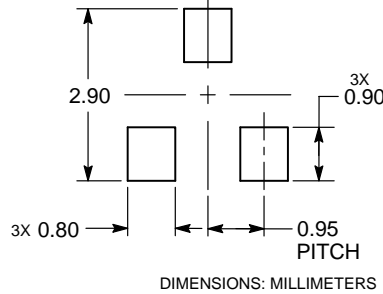
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 21:

1. GATE
2. SOURCE
3. DRAIN

### RECOMMENDED SOLDERING FOOTPRINT



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